

IN THE CLAIMS

Please amend the following claims.

Claims 1-10 (cancelled)

11. (previously presented) A method of making a junction, comprising:
- a) forming a gate electrode on a surface of a substrate, the substrate being of a first conductivity type;
 - b) isotropically etching the substrate such that a recess in the substrate is formed, the recess including a portion that underlies the gate electrode, the recess having a surface;
 - c) selectively forming a layer of a first material having the first conductivity type over the surface of the recess, and within the portion of the recess that underlies the gate electrode; and
 - d) selectively forming a layer of a second material having a second conductivity type over and within the portion that underlies the gate electrode.
12. (cancelled)
13. (previously presented) The method of Claim 11, wherein the substrate comprises silicon doped to have the first conductivity type; the first material comprises doped silicon, and the second material comprises doped silicon.
14. (previously presented) The method of Claim 11, wherein the substrate comprises silicon doped to have the first conductivity type; the first material comprises doped silicon germanium, and the second material comprises doped silicon germanium.
15. (previously presented) The method of Claim 14, wherein the first material has a thickness that is less than a thickness of the second material.
16. (previously presented) The method of Claim 15, wherein the second material has a top surface that is above a plane defined by the surface of the substrate.

17. (original) The method of Claim 11, wherein the patterned structure comprises a dielectric layer and a conductive material disposed over the dielectric layer.
18. (original) The method of Claim 11, wherein etching passivates the surface of the recess.
19. (original) The method of Claim 11, wherein etching comprises exposing the substrate to SF₆ and He in an RF plasma etching system.
20. (original) The method of Claim 11, wherein forming the first material comprises epitaxially depositing a layer of crystalline material.
21. (original) The method of Claim 11, wherein forming the first material comprises epitaxially depositing a layer of crystalline material; and forming the second material comprising epitaxially depositing a layer of crystalline material; wherein the substrate remains unexposed to the atmosphere subsequent to forming the first material and prior to forming the second material.

Claims 22 – 30 (cancelled)